

XPS study of the band alignment at ITO/oxide (n-type MoO₃ or p-type NiO) interface

Submitted by Christian Bernède on Wed, 06/03/2015 - 22:48

Titre	XPS study of the band alignment at ITO/oxide (n-type MoO ₃ or p-type NiO) interface
Type de publication	Article de revue
Auteur	Bernède, Jean Christian [1], Houari, S [2], Nguyen, Duc Tuong [3], Jouan, P Y [4], Khelil, A [5], Mokrani, A [6], Cattin, Linda [7], Predeep, Padmanabhan [8]
Editeur	Wiley
Type	Article scientifique dans une revue à comité de lecture
Année	2012
Langue	Anglais
Numéro	7
Pagination	1291-1297
Volume	209
Titre de la revue	Physica Status Solidi A
Mots-clés	band alignment [9], interfaces [10], Oxides [11], XPS [12] While they have different electronic properties n-type MoO ₃ and p-type NiO are very efficient as buffer layers between the ITO anode and the organic electron donor in organic photovoltaic cells. While it is admitted that MoO ₃ is n-type, its band structure is still under study. Here, the band alignment at the interface of an ITO/MoO ₃ heterojunction is studied by X-ray photoelectron spectroscopy (XPS). The same study is realized on the structure ITO/NiO, NiO being a p-type semiconductor. The measurements have been performed on samples obtained under the same experimental conditions as those used to achieve organic photovoltaic cells. The MoO ₃ (NiO) upper layer was 3 nm thick. The semidirect XPS technique used to measure the band offsets allows us to estimate the band discontinuities at the interface ITO/MoO ₃ : $\Delta E_v = 0.50$ eV and $\Delta E_c = 0.90$ eV, while at the interface ITO/NiO we have $\Delta E_v = -2.10$ eV and $\Delta E_c = -1.90$ eV. Therefore, n-type MoO ₃ and p-type NiO, which are both very efficient anode buffer layers (ABLs), exhibit different band structure at the contact with ITO. However, the measurement, by means of a Kelvin probe, of the work functions of the structures ITO/NiO and ITO/MoO ₃ , shows that they are close and significantly higher than that of ITO alone.
Résumé en anglais	 While they have different electronic properties n-type MoO ₃ and p-type NiO are very efficient as buffer layers between the ITO anode and the organic electron donor in organic photovoltaic cells. While it is admitted that MoO ₃ is n-type, its band structure is still under study. Here, the band alignment at the interface of an ITO/MoO ₃ heterojunction is studied by X-ray photoelectron spectroscopy (XPS). The same study is realized on the structure ITO/NiO, NiO being a p-type semiconductor. The measurements have been performed on samples obtained under the same experimental conditions as those used to achieve organic photovoltaic cells. The MoO ₃ (NiO) upper layer was 3 nm thick. The semidirect XPS technique used to measure the band offsets allows us to estimate the band discontinuities at the interface ITO/MoO ₃ : $\Delta E_v = 0.50$ eV and $\Delta E_c = 0.90$ eV, while at the interface ITO/NiO we have $\Delta E_v = -2.10$ eV and $\Delta E_c = -1.90$ eV. Therefore, n-type MoO ₃ and p-type NiO, which are both very efficient anode buffer layers (ABLs), exhibit different band structure at the contact with ITO. However, the measurement, by means of a Kelvin probe, of the work functions of the structures ITO/NiO and ITO/MoO ₃ , shows that they are close and significantly higher than that of ITO alone.
URL de la notice	http://okina.univ-angers.fr/publications/ua12226 [13]
DOI	10.1002/pssa.201127428 [14]

Liens

- [1] <http://okina.univ-angers.fr/c.bernedele/publications>
- [2] [http://okina.univ-angers.fr/publications?f\[author\]=21405](http://okina.univ-angers.fr/publications?f[author]=21405)
- [3] [http://okina.univ-angers.fr/publications?f\[author\]=21595](http://okina.univ-angers.fr/publications?f[author]=21595)
- [4] [http://okina.univ-angers.fr/publications?f\[author\]=21406](http://okina.univ-angers.fr/publications?f[author]=21406)

- [5] [http://okina.univ-angers.fr/publications?f\[author\]=21395](http://okina.univ-angers.fr/publications?f[author]=21395)
- [6] [http://okina.univ-angers.fr/publications?f\[author\]=21408](http://okina.univ-angers.fr/publications?f[author]=21408)
- [7] [http://okina.univ-angers.fr/publications?f\[author\]=3568](http://okina.univ-angers.fr/publications?f[author]=3568)
- [8] [http://okina.univ-angers.fr/publications?f\[author\]=21409](http://okina.univ-angers.fr/publications?f[author]=21409)
- [9] [http://okina.univ-angers.fr/publications?f\[keyword\]=18074](http://okina.univ-angers.fr/publications?f[keyword]=18074)
- [10] [http://okina.univ-angers.fr/publications?f\[keyword\]=5433](http://okina.univ-angers.fr/publications?f[keyword]=5433)
- [11] [http://okina.univ-angers.fr/publications?f\[keyword\]=5027](http://okina.univ-angers.fr/publications?f[keyword]=5027)
- [12] [http://okina.univ-angers.fr/publications?f\[keyword\]=9616](http://okina.univ-angers.fr/publications?f[keyword]=9616)
- [13] <http://okina.univ-angers.fr/publications/ua12226>
- [14] <http://dx.doi.org/10.1002/pssa.201127428>

Publié sur *Okina* (<http://okina.univ-angers.fr>)